

SILICON EPITAXIAL PLANAR DIODE

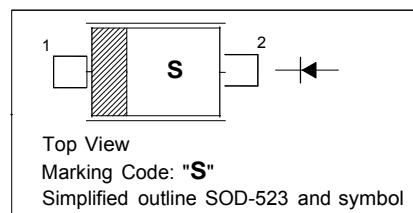
Band Switching Diode

Applications

- For VHF tuner band RF attenuator
- AGC for FM tuner

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	50	V
Forward Current	I_F	50	mA
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Voltage at $I_R = 10 \mu\text{A}$	V_R	50	-	-	V
Reverse Current at $V_R = 50 \text{ V}$	I_R	-	-	0.1	μA
Total Capacitance at $V_R = 50 \text{ V}$, $f = 1 \text{ MHz}$	C_T	-	0.25	-	pF
Series Resistance at $I_F = 5 \text{ mA}$, $f = 100 \text{ MHz}$	r_s	-	1.5	-	Ω

Fig. 1 I_c-T_a

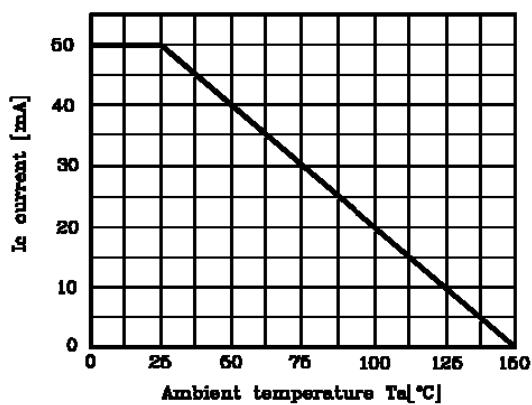


Fig. 2 I_F-V_F

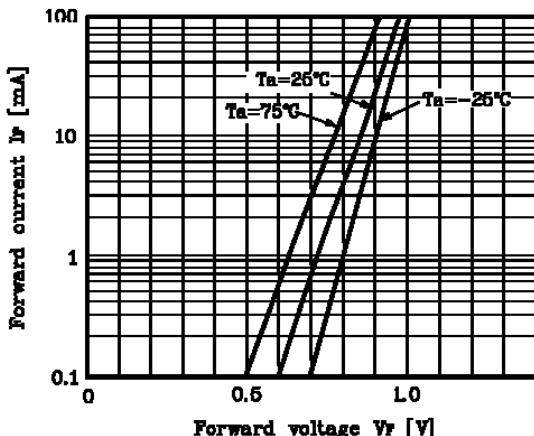


Fig. 3 C_T-V_R

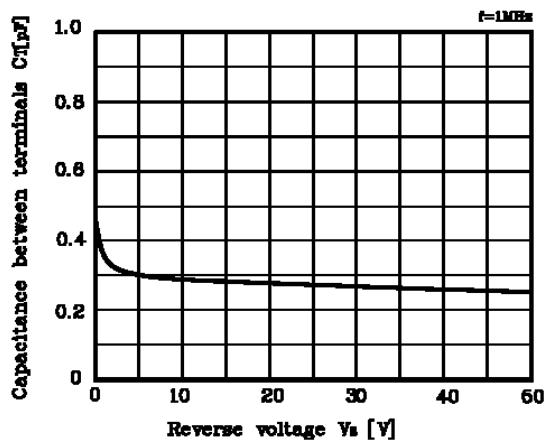


Fig. 4 r_s-I_F

